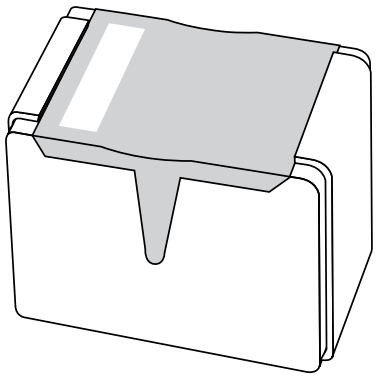
DATA SHEET



BAS216
High-speed switching diode

Product specification
Supersedes data of 1999 Apr 22

2002 May 28

Philips
Semiconductors

PHILIPS

High-speed switching diode BAS216

FEATURES

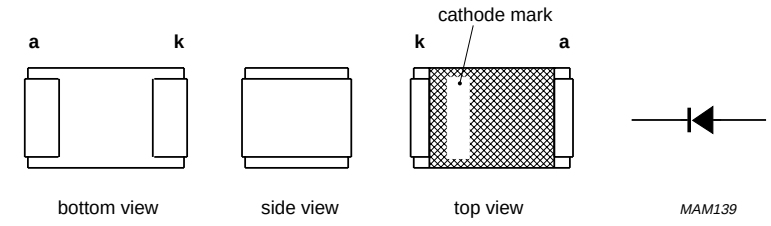
- Small ceramic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATIONS

- High-speed switching in e.g. surface mounted circuits.

DESCRIPTION

The BAS216 is a high-speed switching diode fabricated in planar technology, and encapsulated in the SOD110 very small rectangular ceramic SMD package.



Marking code: A6.

Fig.1 Simplified outline (SOD110) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		–	85	V
V_R	continuous reverse voltage		–	75	V
I_F	continuous forward current	note 1	–	250	mA
I_{FRM}	repetitive peak forward current		–	500	mA
I_{FSM}	non-repetitive peak forward current	square wave; T_j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	–	4	A
		t = 1 ms	–	1	A
		t = 1 s	–	0.5	A
P_{tot}	total power dissipation	T_{amb} = 25 °C; see Fig.2; note 1	–	400	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

ELECTRICAL CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_F	forward voltage	see Fig.3			
		I_F = 1 mA	–	715	mV
		I_F = 10 mA	–	855	mV
		I_F = 50 mA	–	1	V
		I_F = 150 mA	–	1.25	V
I_R	reverse current	see Fig.5			
		V_R = 25 V	–	30	nA
		V_R = 75 V	–	1	µA
		V_R = 25 V; T_j = 150 °C	–	30	µA
		V_R = 75 V; T_j = 150 °C	–	50	µA
C_d	diode capacitance	f = 1 MHz; V_R = 0; see Fig.6	–	1.5	pF
t_{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA; see Fig.7	–	4	ns
V_{fr}	forward recovery voltage	when switched from I_F = 10 mA; t_r = 20 ns; see Fig.8	–	1.75	V

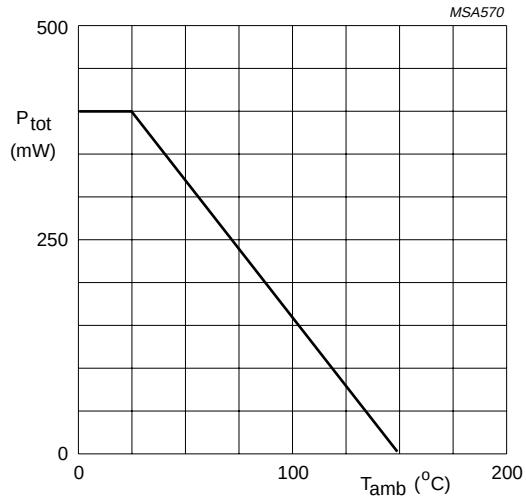
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}tp}$	thermal resistance from junction to tie-point		200	K/W
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	315	K/W

Note

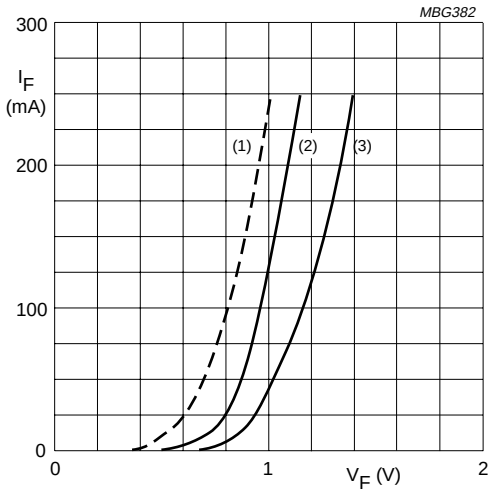
1. Device mounted on an FR4 printed-circuit board.

GRAPHICAL DATA



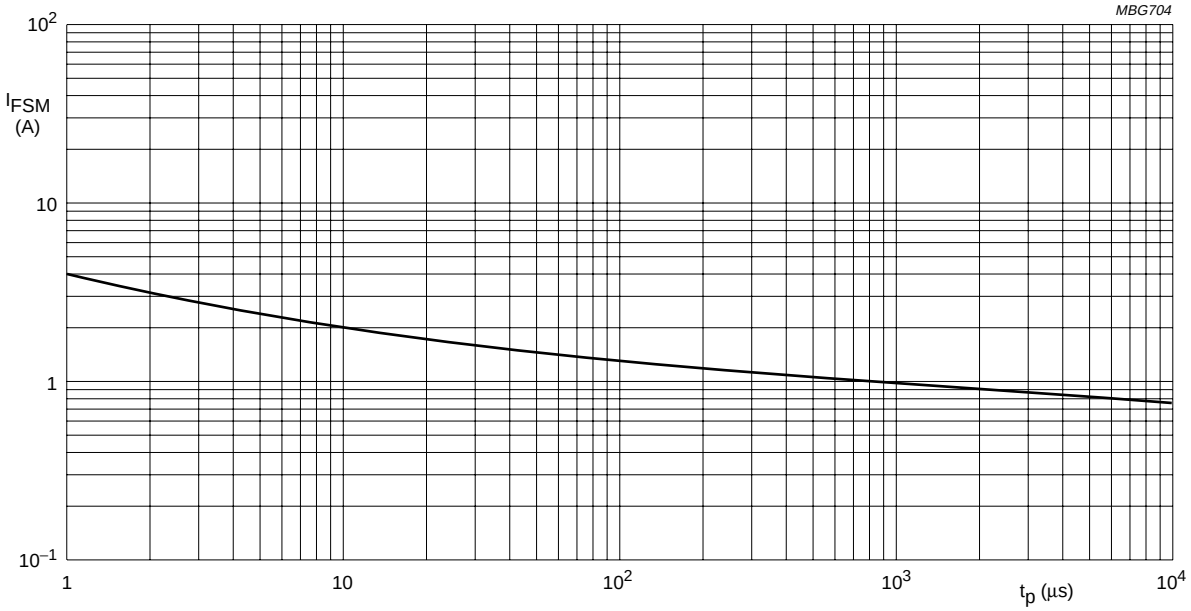
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible total power dissipation as a function of ambient temperature.



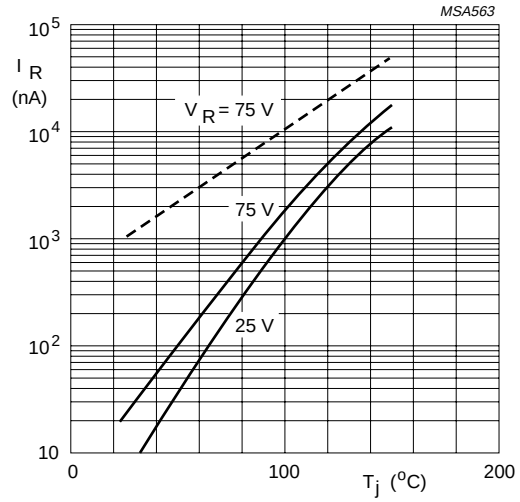
(1) T_j = 150 °C; typical values.
(2) T_j = 25 °C; typical values.
(3) T_j = 25 °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



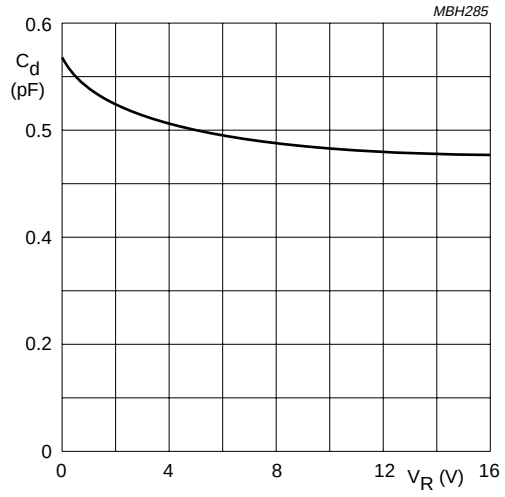
Based on square wave currents.
T_j = 25 °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.



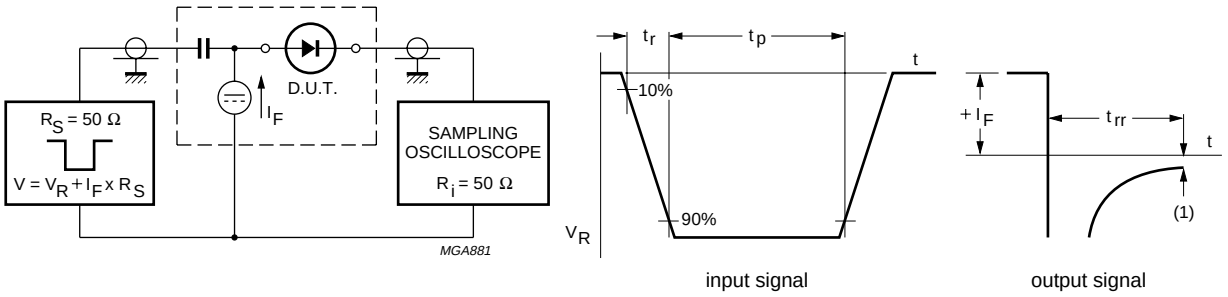
Dotted line: maximum values.
Solid lines: typical values.

Fig.5 Reverse current as a function of junction temperature.



f = 1 MHz; T_j = 25 °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.



(1) I_R = 1 mA.

Fig.7 Reverse recovery voltage test circuit and waveforms.

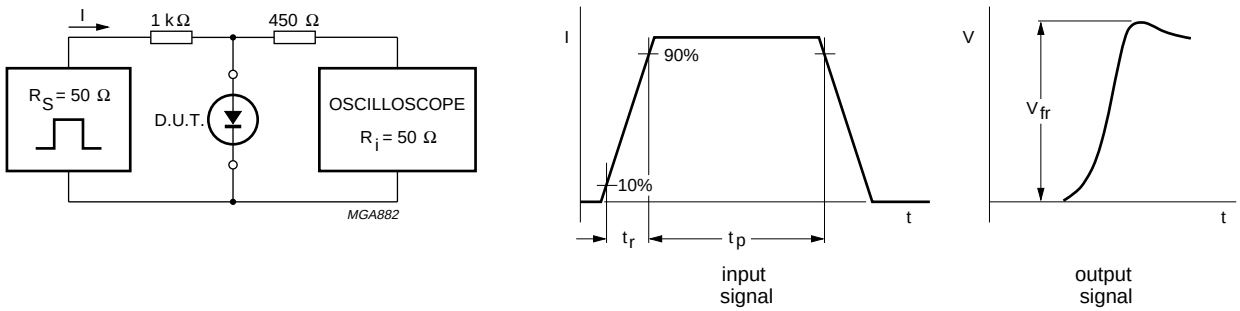
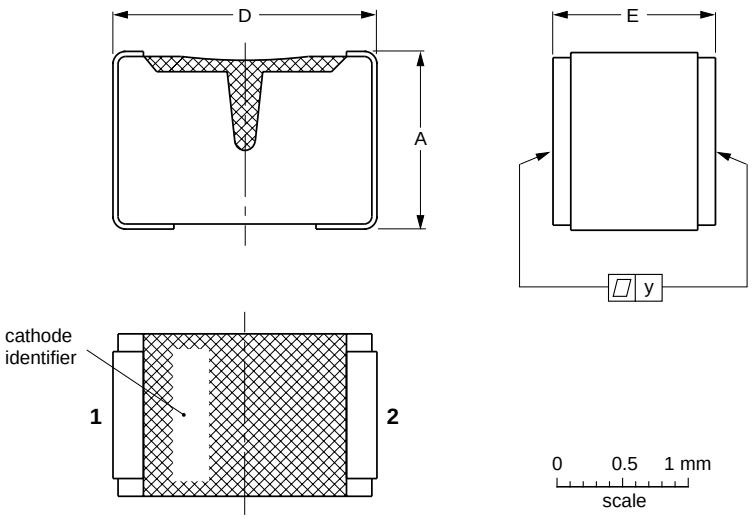


Fig.8 Forward recovery voltage test circuit and waveforms.

PACKAGE OUTLINE

Very small ceramic rectangular surface mounted package **SOD110**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	D	E	y
mm	1.6	2.10 1.90	1.40 1.10	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOD110						97-04-14

DATA SHEET STATUS

DATA SHEET STATUS[1]	PRODUCT STATUS[2]	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Notes

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2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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